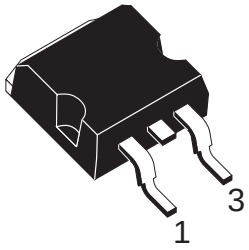
STB60NF03L

N-CHANNEL 30V - 0.008Ω - 60A D2PAK
STripFET™ POWER MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STB60NF03L	30 V	< 0.01 Ω	60 A

- TYPICAL $R_{DS}(on)$ = 0.008 Ω
- LOW THRESHOLD DRIVE

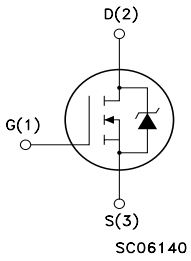


D^2PAK

DESCRIPTION

This Power Mosfet is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalance characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- MOTOR CONTROL,AUDIO AMPLIFIERS
- DC-DC & DC-AC CONVERTERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	30	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	30	V
V_{GS}	Gate- source Voltage	± 20	V
I_D	Drain Current (continuos) at T_C = 25°C	60	A
I_D	Drain Current (continuos) at T_C = 100°C	42	A
I_{DM} (●)	Drain Current (pulsed)	240	A
P_{TOT}	Total Dissipation at T_C = 25°C	100	W
	Derating Factor	0.67	W/°C
E_{AS} (1)	Single Pulse Avalanche Energy	650	mJ
T_{stg}	Storage Temperature	–65 to 175	°C
T_j	Max. Operating Junction Temperature	175	°C

(●) Pulse width limited by safe operating area

(1) Starting T_j=25°C, I_D=30A, V_{DD}=20V

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1.5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
Rthj-sink	Thermal Resistance case-sink Max	0.5	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300	°C

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	30			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			1	µA
		V_{DS} = Max Rating, T_C = 125 °C			10	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20 V			± 100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	1	1.5	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V, I_D = 30 A		0.008	0.010	Ω
		V_{GS} = 4.5 V, I_D = 30 A		0.0095	0.015	Ω
$I_{D(on)}$	On State Drain Current	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max}$, V_{GS} = 10V	60			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max}$, I_D = 30 A		60		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		2550		pF
C_{oss}	Output Capacitance			630		pF
C_{rss}	Reverse Transfer Capacitance			215		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 15 V, I_D = 30 A		40		ns
t_r	Rise Time	R_G = 4.7Ω V_{GS} = 4.5 V (see test circuit, Figure 3)		250		ns
Q_g	Total Gate Charge	V_{DD} = 24 V, I_D = 60A,		43	58	nC
Q_{gs}	Gate-Source Charge	V_{GS} = 5V		12		nC
Q_{gd}	Gate-Drain Charge			21		nC

SWITCHING OFF

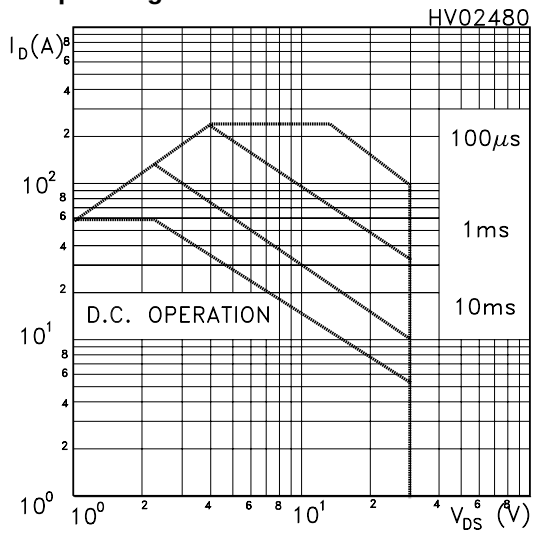
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	V_{DD} = 15 V, I_D = 30 A,		60		ns
t_f	Fall Time	R_G = 4.7Ω, V_{GS} = 4.5V (see test circuit, Figure 3)		70		ns

SOURCE DRAIN DIODE

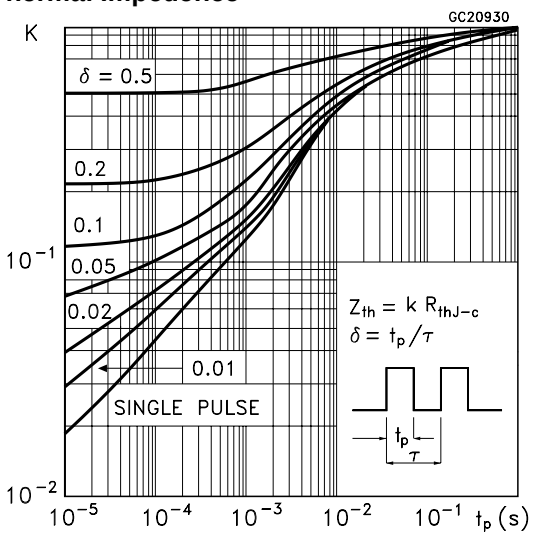
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				60	A
I_{SDM} (1)	Source-drain Current (pulsed)				240	A
V_{SD} (2)	Forward On Voltage	I_{SD} = 60 A, V_{GS} = 0			1.5	V
t_{rr}	Reverse Recovery Time	I_{SD} = 60 A, di/dt = 100A/µs,		75		ns
Q_{rr}	Reverse Recovery Charge	V_{DD} = 15 V, T_j = 150°C		100		nC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		2.6		A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

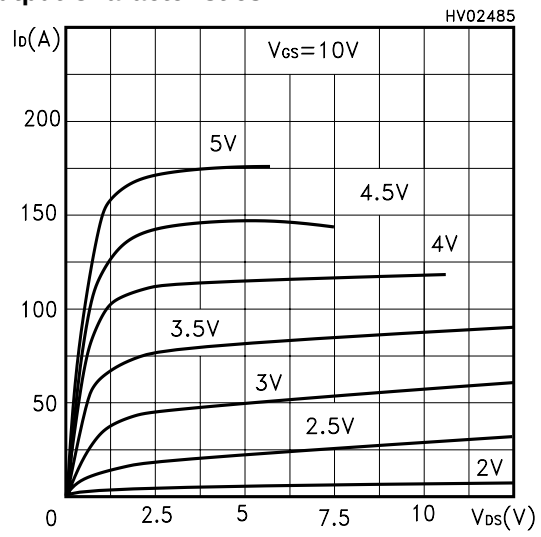
Safe Operating Area



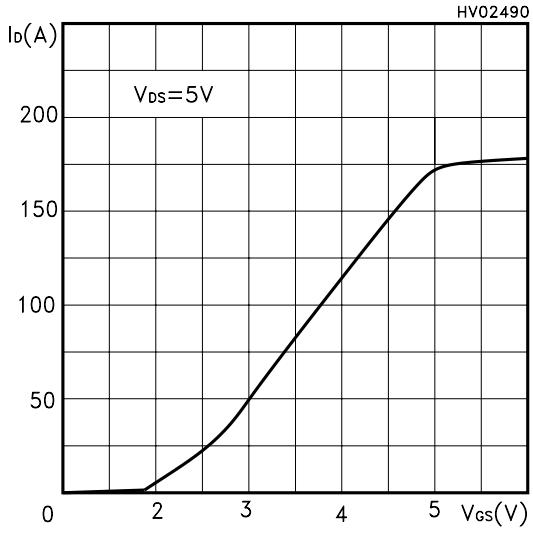
Thermal Impedence



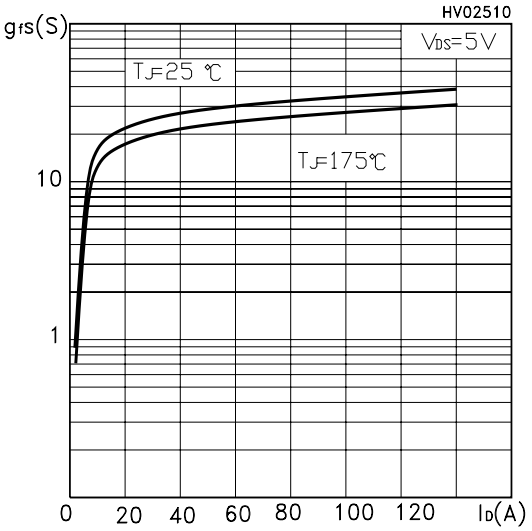
Output Characteristics



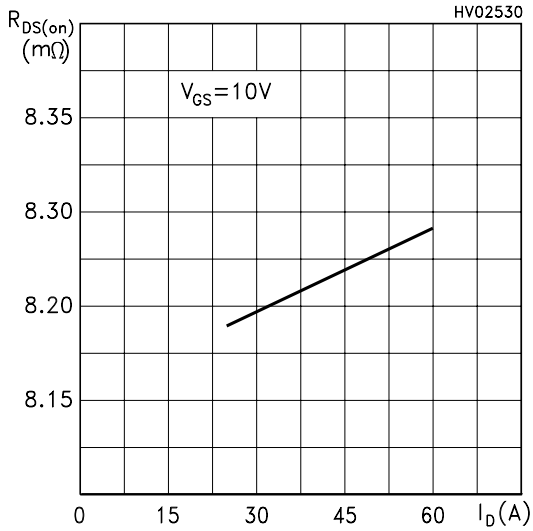
Transfer Characteristics



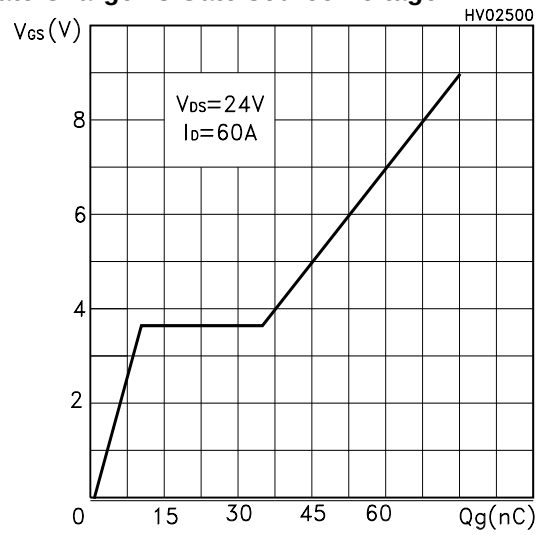
Transconductance



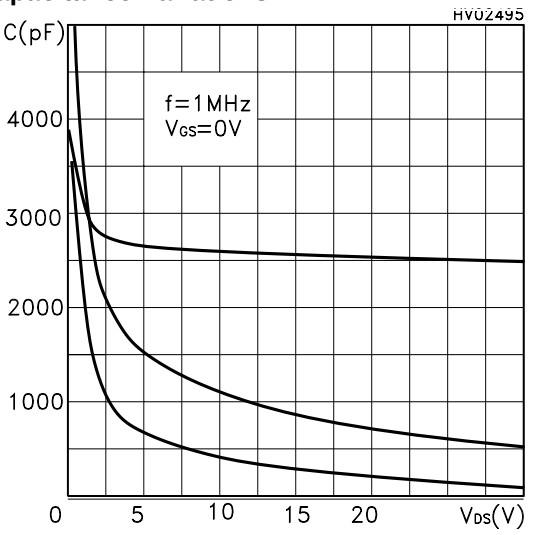
Static Drain-source On Resistance



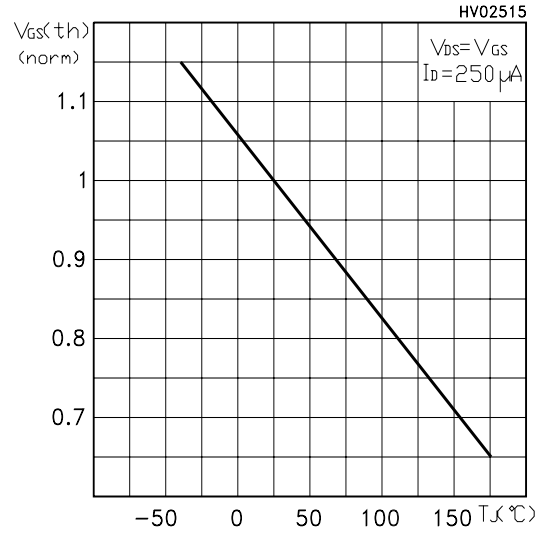
Gate Charge vs Gate-source Voltage



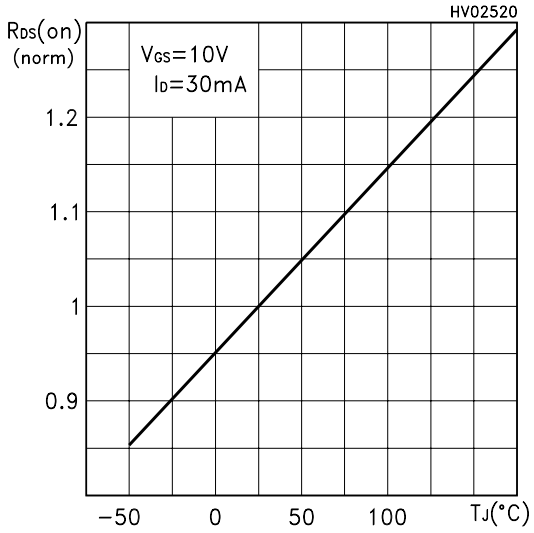
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

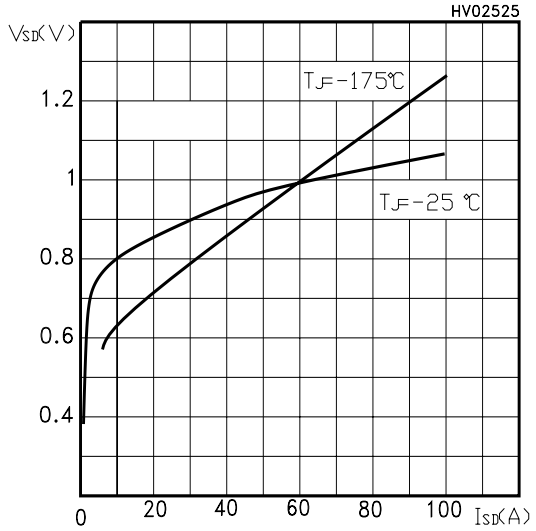


Fig. 1: Unclamped Inductive Load Test Circuit

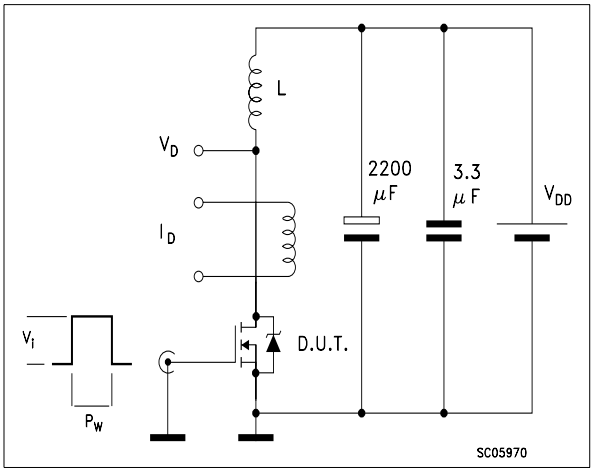


Fig. 2: Unclamped Inductive Waveform

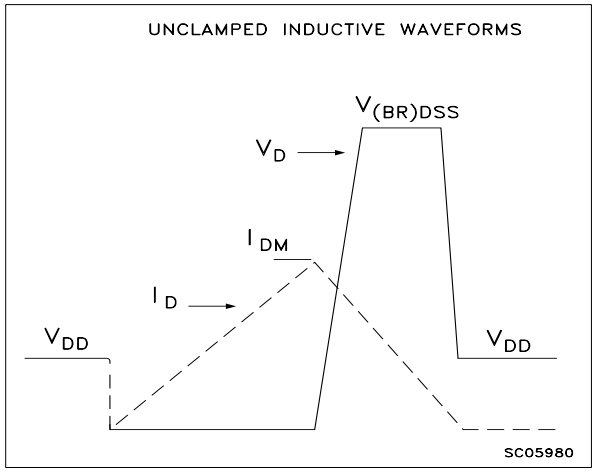


Fig. 3: Switching Times Test Circuit For Resistive Load

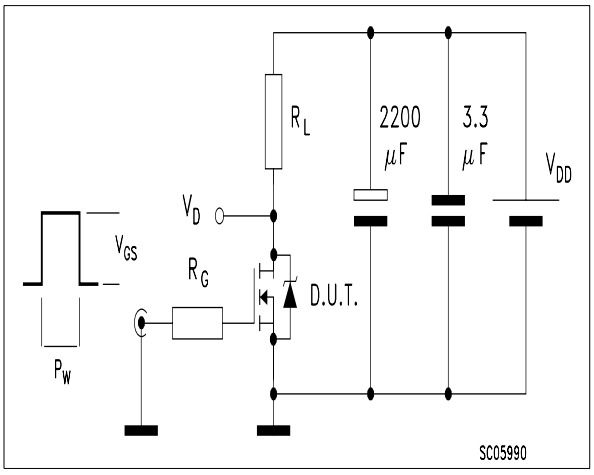


Fig. 4: Gate Charge test Circuit

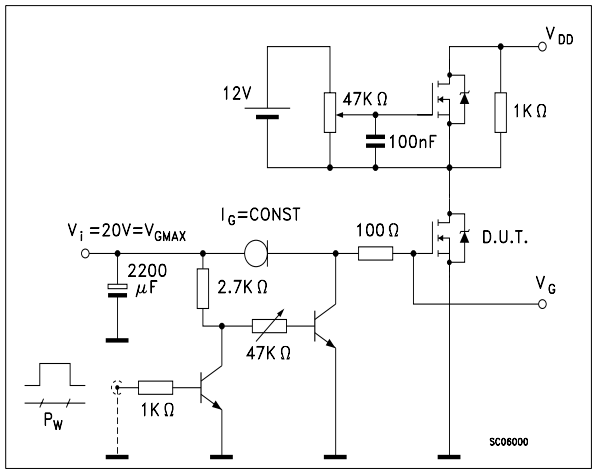
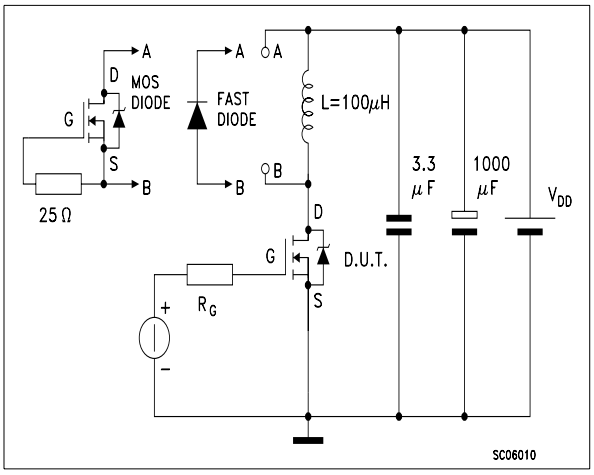


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		8º